

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07600 DT-33-13

SILICON NPN TRIPLE DIFFUSED TYPE

2SC2791

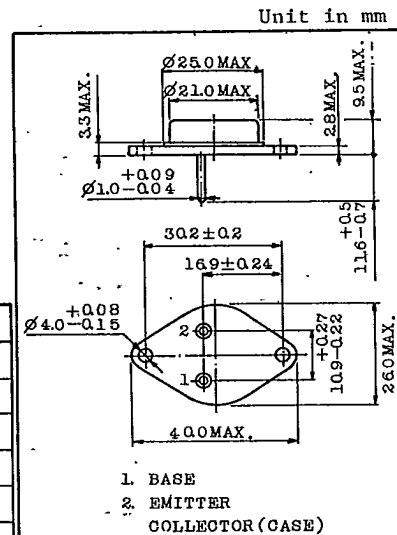
HIGH SPEED AND HIGH VOLTAGE SWITCHING APPLICATIONS.
SWITCHING REGULATOR APPLICATIONS.
HIGH SPEED DC-DC CONVERTER APPLICATIONS.

FEATURES:

- Excellent Switching Times : $t_r=1.0\mu s$ (Max.); $t_f=1.0\mu s$ (Max.) ($I_C=3A$)
• High Collector Breakdown Voltage : $V_{CEO}=800V$

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	900	V
Collector-Emitter Voltage	V _{CE0}	800	V
Emitter-Base Voltage	V _{EB0}	7	V
Collector Current	I _C	5	A
Base Current	I _B	3	A
Collector Power Dissipation (T _c =25°C)	P _C	100	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



J EDEC	TO-204MA/TO-3
EIAJ	TC-3, TB-3
TOSHIBA	2-21E1A

MOUNTING KIT No. AC100
Weight : 16g

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

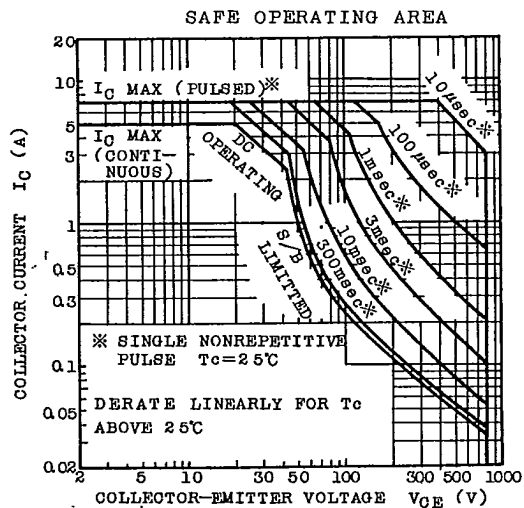
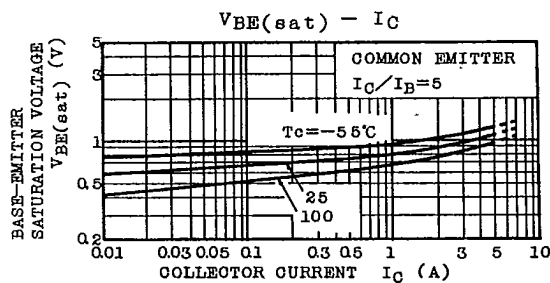
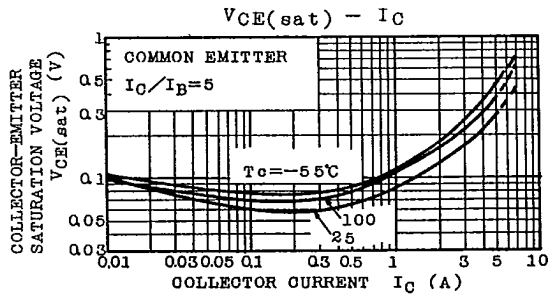
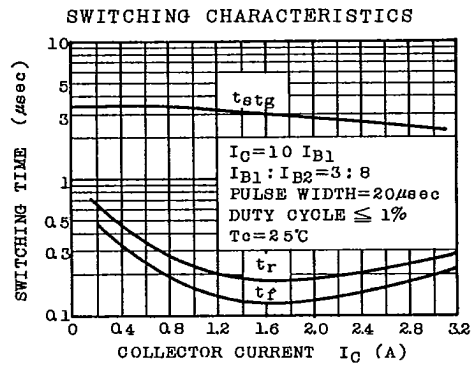
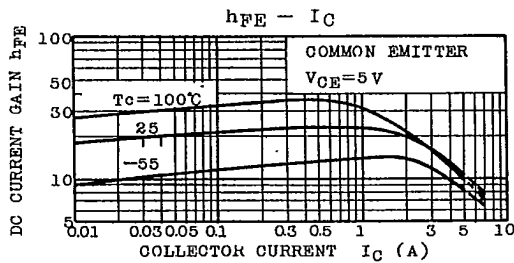
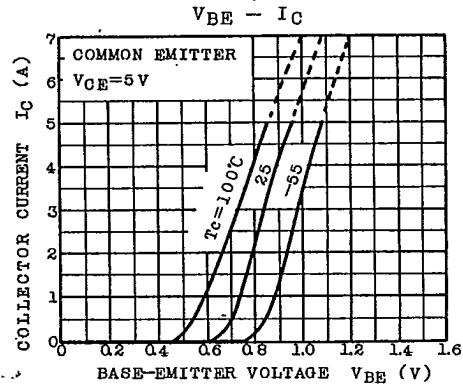
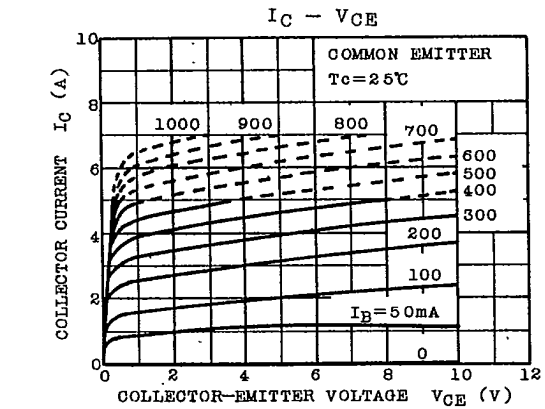
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =800V, I _E =0	-	-	100	μ A
Emitter Cut-off Current		IEBO	V _{EB} =7V, I _C =0	-	-	1	mA
Collector-Base Breakdown Voltage		V(BR)CBO	I _C =1mA, I _E =0	900	-	-	V
Collector-Emitter Breakdown Voltage		V(BR)CEO	I _C =10mA, I _B =0	800	-	-	V
DC Current Gain		hFE(1)	V _{CE} =5V, I _C =10mA (Note)	10	-	-	
		hFE(2)	V _{CE} =5V, I _C =3A (Note)	10	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =3A, I _B =0.6A (Note)	-	-	1.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}	I _C =3A, I _B =0.6A (Note)	-	-	1.5	V
Switching Time	Rise Time	t _r	$V_{OG}=400V$ $I_O=3A$ $DUTY\ CYCLE \leq 1\%$	-	-	1.0	μs
	Storage Time	t _{stg}		-	-	3.5	
	Fall Time	t _f		-	-	1.0	

Note : Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

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